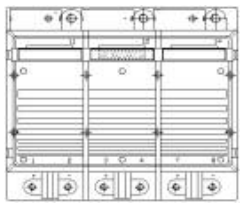
SKiiP 232GD120-313CTV ...



SKiiP® 2

6-pack - integrated intelligent Power System

Power section

SKiiP 232GD120-313CTV

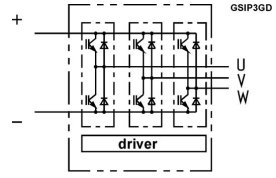
Features

- SKiiP technology inside
- Low loss IGBTs
- CAL diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 2 System)
- IEC 68T.1 (climate) 40/125/56 (SKiiP® 2 power section)

1) with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)

Absolute Maximum Ratings		T_s = 25 °C unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
IGBT			
V_{CES}		1200	V
V_{CC} 1)	Operating DC link voltage	900	V
V_{GES}		± 20	V
I_C	T_s = 25 (70) °C	200 (150)	A
Inverse diode			
I_F = - I_C	T_s = 25 (70) °C	200 (150)	A
I_{FSM}	T_j = 150 °C, t_p = 10 ms; sin.	1440	A
I²t (Diode)	Diode, T_j = 150 °C, 10 ms	10	kA²s
T_j, (T_{stg})		- 40 (- 25) ... + 150 (125)	°C
V_{isol}	AC, 1 min. (mainterminals to heat sink)	3000	V

Characteristics		T_s = 25 °C unless otherwise specified			
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT					
V_{CEsat}	I_C = 175 A, T_j = 25 (125) °C		2,6 (3,1)	3,1	V
V_{CEO}	T_j = 25 (125) °C		1,2 (1,3)	1,5 (1,6)	V
r_{CE}	T_j = 25 (125) °C		7,5 (10)	9 (11,5)	mΩ
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}, T_j = 25 (125) °C		(10)	0,4	mA
E_{on} + E_{off}	I_C = 175 A, V_{CC} = 600 V			53	mJ
	T_j = 125 °C, V_{CC} = 900 V			93	mJ
$R_{CC'+EE'}$	terminal chip, T_j = 125 °C		0,5		mΩ
L_{CE}	top, bottom		15		nH
C_{CHC}	per phase, AC-side		1,4		nF
Inverse diode					
V_F = V_{EC}	I_F = 150 A, T_j = 25 (125) °C		2,1 (1,9)	2,6	V
V_{TO}	T_j = 25 (125) °C		1,3 (1)	1,4 (1,1)	V
r_T	T_j = 25 (125) °C		5 (6)	6,8 (7,8)	mΩ
E_{rr}	I_C = 175 A, V_{CC} = 600 V			7	mJ
	T_j = 125 °C, V_{CC} = 900 V			9	mJ
Mechanical data					
M_{dc}	DC terminals, SI Units	6		8	Nm
M_{ac}	AC terminals, SI Units	13		15	Nm
w	SKiiP® 2 System w/o heat sink		2,7		kg
w	heat sink		6,6		kg
Thermal characteristics (P16 heat sink; 295 m³/h); " $_r$ " reference to temperature sensor					
$R_{th(j-s)I}$	per IGBT			0,129	K/W
$R_{th(j-s)D}$	per diode			0,375	K/W
$R_{th(s-a)}$	per module			0,036	K/W
Z_{th}	R_i (mK/W) (max. values)			tau$_i$(s)	
	1 2 3 4			1 2 3 4	
$Z_{th(j-r)I}$	14 99 15			1 0,13 0,001	
$Z_{th(j-r)D}$	41 289 45			1 0,13 0,001	
$Z_{th(r-a)}$	11,1 18,3 3,5 3,1			204 60 6 0,02	



Case S 3

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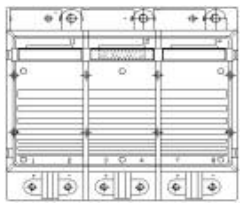

SKiiP® 2

6-pack - integrated intelligent Power System

6-pack
integrated gate driver

SKiiP 232GD120-313CTV

Gate driver features

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 68T.1 (climate) 25/85/56 (SKiiP® 2 gate driver)

Absolute Maximum Ratings

Symbol	Conditions	Values	Units
V_{S1}	stabilized 15 V power supply	18	V
V_{S2}	unstabilized 24 V power supply	30	V
V_{iH}	input signal voltage (high)	15 + 0,3	V
dv/dt	secondary to primary side	75	kV/µs
V_{isolIO}	input / output (AC, r.m.s., 2s)	3000	Vac
V_{isol12}	output 1 / output 2 (AC, r.m.s., 2s)	1500	Vac
f_{max}	switching frequency	20	kHz
T_{op} (T_{stg})	operating / storage temperature	- 25 ... + 85	°C

Characteristics (T_a = 25 °C)

Symbol	Conditions	min.	typ.	max.	Units
V_{S1}	supply voltage stabilized	14,4	15	15,6	V
V_{S2}	supply voltage non stabilized	20	24	30	V
I_{S1}	V_{S1} = 15 V		340+360*f/f_{max}+3,5*(I_{AC}/A)		mA
I_{S2}	V_{S2} = 24 V		250+250*f/f_{max}+2,6*(I_{AC}/A)		mA
V_{iT+}	input threshold voltage (High)	11,2			V
V_{iT-}	input threshold voltage (Low)			5,4	V
R_{IN}	input resistance		10		kΩ
$t_{d(on)IO}$	input-output turn-on propagation time		1,2		µs
$t_{d(off)IO}$	input-output turn-off propagation time		1,6		µs
$t_{pERRRESET}$	error memory reset time	9			µs
t_{TD}	top / bottom switch : interlock time		2,3		µs
$I_{analogOUT}$	8 V corresponds to max. current of 15 V supply voltage		200		A
$I_{Vs1outmax}$	(available when supplied with 24 V)			50	mA
I_{A0max}	output current at pin 13/20/22/24/26			5	mA
V_{0l}	logic low output voltage			0,6	V
V_{0H}	logic high output voltage			30	V
I_{TRIPSC}	over current trip level ($I_{analog\ OUT}$ = 10 V)		250		A
I_{TRIPLG}	ground fault protection		58		A
T_{tp}	over temperature protection	110		120	°C
U_{DCTRIP}	trip level of U_{DC}-protection ($U_{analog\ OUT}$ = 9 V); (option)	900			V

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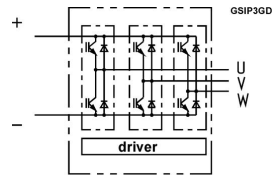

Case S 3

